Microchip Technology - A3P1000-1FGG484T Datasheet

Welcome to E-XFL.COM

Understanding Embedded - FPGAs (Field Programmable Gate Array)

Embedded - FPGAs, or Field Programmable Gate Arrays, are advanced integrated circuits that offer unparalleled flexibility and performance for digital systems. Unlike traditional fixed-function logic devices, FPGAs can be programmed and reprogrammed to execute a wide array of logical operations, enabling customized functionality tailored to specific applications. This reprogrammability allows developers to iterate designs quickly and implement complex functions without the need for custom hardware.

Applications of Embedded - FPGAs

The versatility of Embedded - FPGAs makes them indispensable in numerous fields. In telecommunications,

Details	
Product Status	Active
Number of LABs/CLBs	-
Number of Logic Elements/Cells	-
Total RAM Bits	147456
Number of I/O	300
Number of Gates	1000000
Voltage - Supply	1.425V ~ 1.575V
Mounting Type	Surface Mount
Operating Temperature	-40°C ~ 125°C (TA)
Package / Case	484-BGA
Supplier Device Package	484-FPBGA (23x23)
Purchase URL	https://www.e-xfl.com/product-detail/microchip-technology/a3p1000-1fgg484t

Temperature Grade Offerings

Package	A3P060	A3P125	A3P250	A3P1000
VQ100	C, I, T	C, I, T	C, I, T	–
FG144	C, I, T	C, I, T	C, I, T	C, I, T
FG256	–	–	C, I, T	C, I, T
FG484	–	–	–	C, I, T
QNG132	–	C, I, T	C, I, T	–

Notes:

1. *C = Commercial temperature range: 0°C to 70°C*
2. *I = Industrial temperature range: –40°C to 85°C*
3. *T = Automotive temperature range: Grade 2 and Grade 1 AEC-Q100*
   Grade 2 = 105°C T_A and 115°C T_J
   Grade 1 = 125°C T_A and 135°C T_J
4. *Specifications for Commercial and Industrial grade devices can be found in the* ProASIC3 Flash Family FPGAs *datasheet.*

Speed Grade and Temperature Grade Matrix

Temperature Grade	Std.	–1
T (Grade 1 and Grade 2), Commercial, Industrial	3	3

Notes:

1. *T = Automotive temperature range: Grade 2 and Grade 1 AEC-Q100*
   Grade 2 = 105°C T_A and 115°C T_J
   Grade 1 = 125°C T_A and 135°C T_J
2. *Specifications for Commercial and Industrial grade devices can be found in the* ProASIC3 Flash Family FPGAs *datasheet.*

Contact your local Microsemi SoC Products Group representative for device availability:
http://www.microsemi.com/soc/contact/default.aspx.

Table of Contents

Automotive ProASIC3 Device Family Overview

General Description 1-1

Automotive ProASIC3 DC and Switching Characteristics

General Specifications 2-1
Calculating Power Dissipation 2-6
User I/O Characteristics 2-12
VersaTile Characteristics 2-69
Global Resource Characteristics 2-75
Clock Conditioning Circuits 2-80
Embedded SRAM and FIFO Characteristics 2-82
Embedded FlashROM Characteristics 2-96
JTAG 1532 Characteristics 2-97

Pin Descriptions and Packaging

Supply Pins 3-1
User Pins 3-2
JTAG Pins 3-3
Special Function Pins 3-4
Packaging 3-4
Related Documents 3-4

Package Pin Assignments

VQ100 4-1
QN132 4-5
FG144 4-10
FG256 4-19
FG484 4-26

Datasheet Information

List of Changes 5-1
Datasheet Categories 5-4
Safety Critical, Life Support, and High-Reliability Applications Policy 5-4

Advanced Architecture

The proprietary Automotive ProASIC3 architecture provides granularity comparable to standard-cell ASICs. The Automotive ProASIC3 device consists of five distinct and programmable architectural features (Figure 1-1 and Figure 1-2 on page 1-4):

- FPGA VersaTiles
- Dedicated FlashROM
- Dedicated SRAM memory
- Extensive CCCs and PLLs
- Advanced I/O structure

The FPGA core consists of a sea of VersaTiles. Each VersaTile can be configured as a three-input logic function, a D-flip-flop (with or without enable), or a latch by programming the appropriate flash switch interconnections. The versatility of the Automotive ProASIC3 core tile as either a three-input lookup table (LUT) equivalent or a D-flip-flop/latch with enable allows for efficient use of the FPGA fabric. The VersaTile capability is unique to the Microsemi ProASIC family of third-generation-architecture flash FPGAs. VersaTiles are connected with any of the four levels of routing hierarchy. Flash switches are distributed throughout the device to provide nonvolatile, reconfigurable interconnect programming. Maximum core utilization is possible for virtually any design.

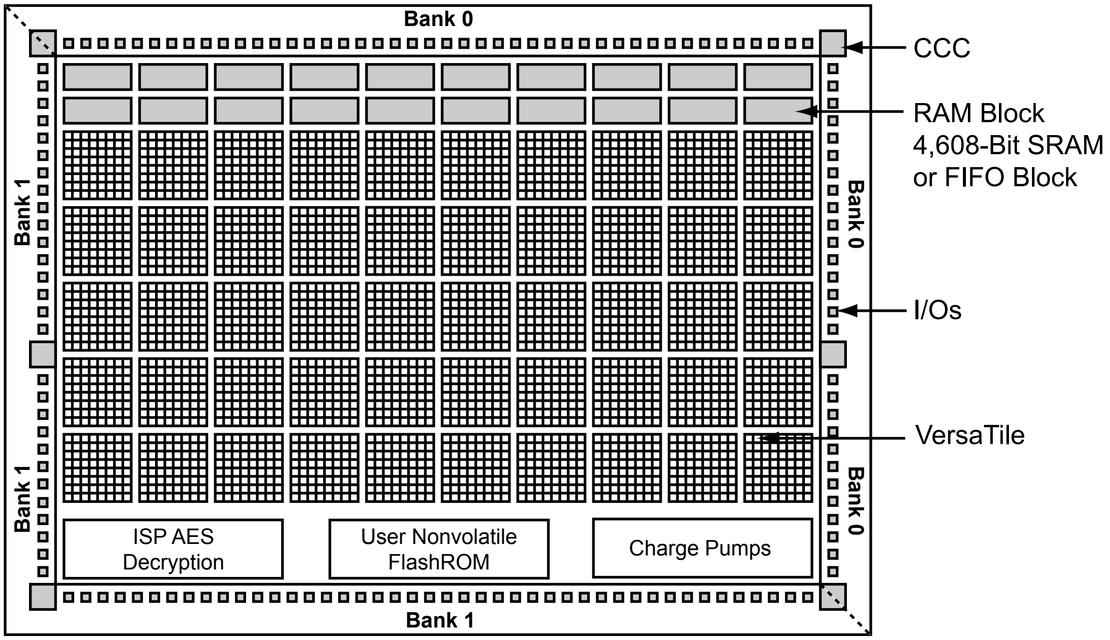


Figure 1-1 • **Automotive ProASIC3 Device Architecture Overview with Two I/O Banks (A3P060 and A3P125)**

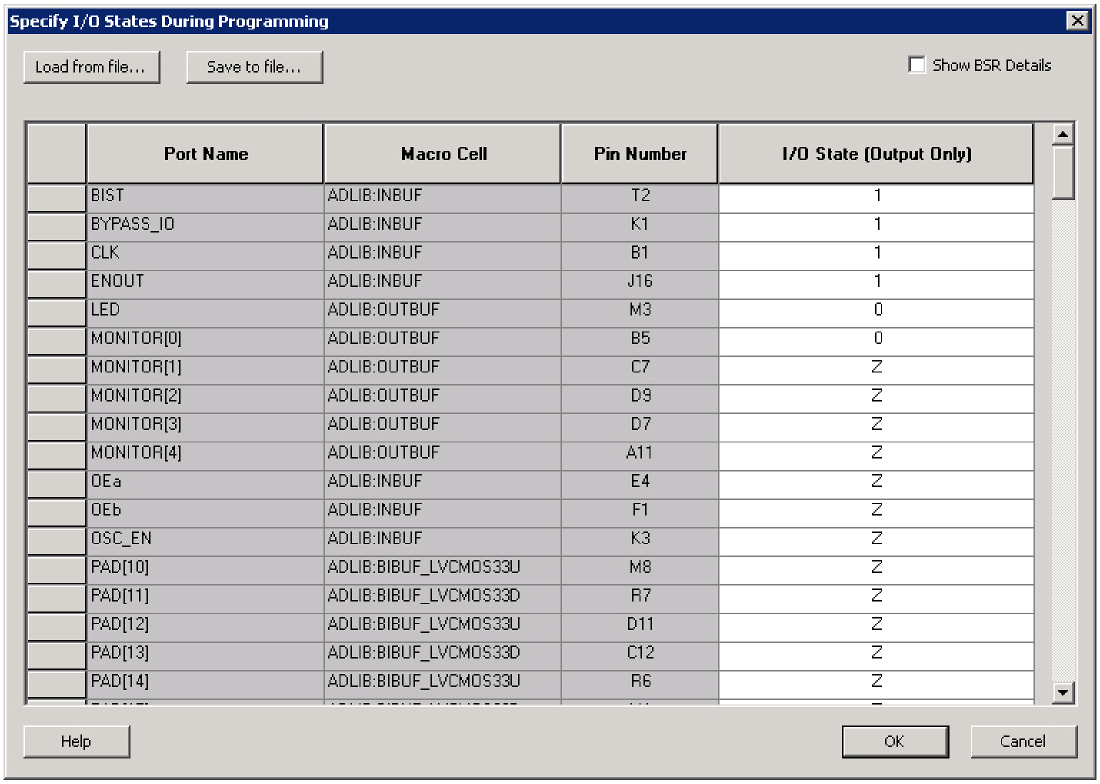
5. Set the I/O Output State. You can set Basic I/O settings if you want to use the default I/O settings for your pins, or use Custom I/O settings to customize the settings for each pin. Basic I/O state settings:

   1 – I/O is set to drive out logic High

   0 – I/O is set to drive out logic Low

   Last Known State – I/O is set to the last value that was driven out prior to entering the programming mode, and then held at that value during programming

   Z -Tristate: I/O is tristated



Port Name	Macro Cell	Pin Number	I/O State (Output Only)
BIST	ADLIB:INBUF	T2	1
BYPASS_IO	ADLIB:INBUF	K1	1
CLK	ADLIB:INBUF	B1	1
ENOUT	ADLIB:INBUF	J16	1
LED	ADLIB:OUTBUF	M3	0
MONITOR[0]	ADLIB:OUTBUF	B5	0
MONITOR[1]	ADLIB:OUTBUF	C7	Z
MONITOR[2]	ADLIB:OUTBUF	D9	Z
MONITOR[3]	ADLIB:OUTBUF	D7	Z
MONITOR[4]	ADLIB:OUTBUF	A11	Z
OEa	ADLIB:INBUF	E4	Z
OEb	ADLIB:INBUF	F1	Z
OSC_EN	ADLIB:INBUF	K3	Z
PAD[10]	ADLIB:BIBUF_LVCMOS33U	M8	Z
PAD[11]	ADLIB:BIBUF_LVCMOS33D	R7	Z
PAD[12]	ADLIB:BIBUF_LVCMOS33U	D11	Z
PAD[13]	ADLIB:BIBUF_LVCMOS33D	C12	Z
PAD[14]	ADLIB:BIBUF_LVCMOS33U	R6	Z

Figure 1-4 • **I/O States During Programming Window**

6. Click **OK** to return to the FlashPoint – Programming File Generator window.

Note: I/O States During programming are saved to the ADB and resulting programming files after completing programming file generation.

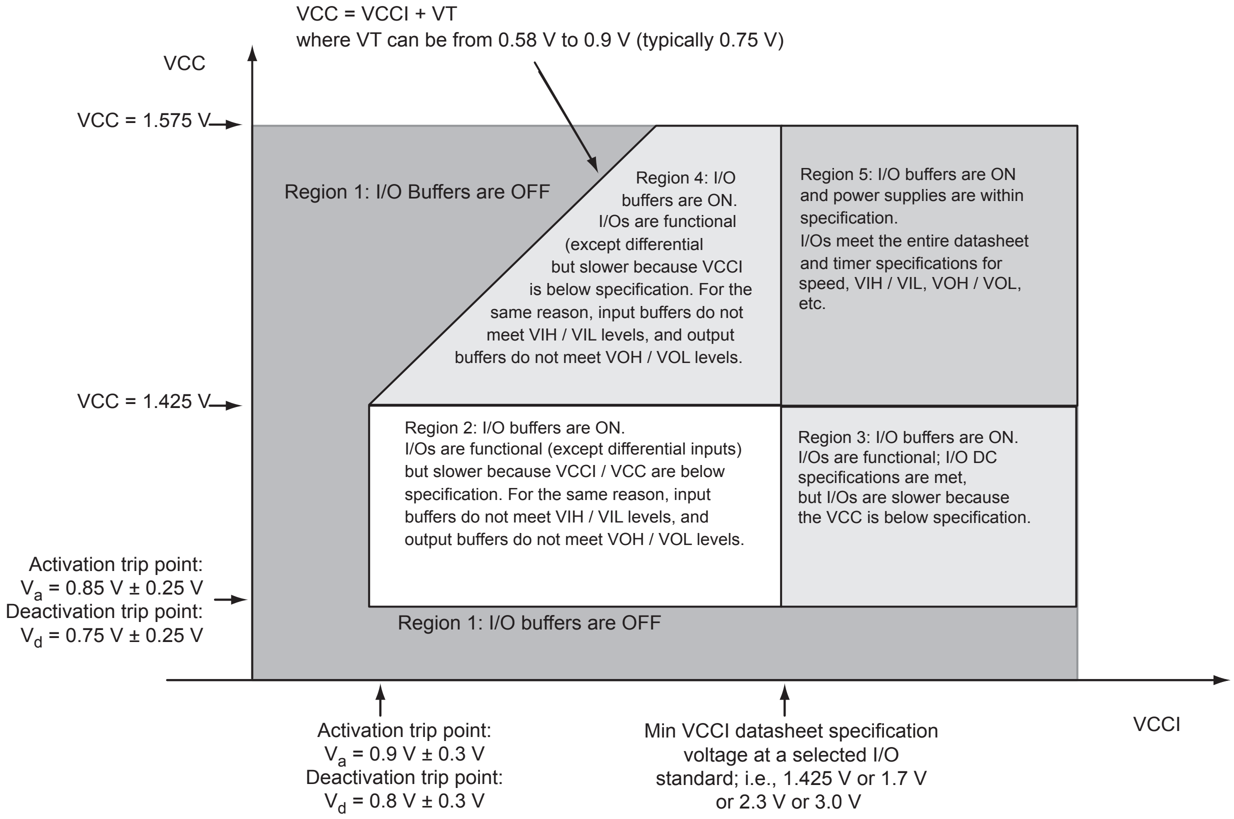


Figure 2-2 • **I/O State as a Function of VCCI and VCC Voltage Levels**

Thermal Characteristics

Introduction

The temperature variable in Designer software refers to the junction temperature, not the ambient temperature. This is an important distinction because dynamic and static power consumption cause the chip junction to be higher than the ambient temperature.

EQ 1 can be used to calculate junction temperature.

$$T_J = \text{Junction Temperature} = \Delta T + T_A$$

EQ 1

where:

T_A = Ambient Temperature

ΔT = Temperature gradient between junction (silicon) and ambient $\Delta T = \theta_{ja} * P$

θ_{ja} = Junction-to-ambient of the package. θ_{ja} numbers are located in Table 2-4 on page 2-5.

P = Power dissipation

Table 2-22 • Summary of I/O Timing Characteristics—Software Default Settings
–1 Speed Grade, Automotive-Case Conditions: T_J = 135°C, Worst Case VCC = 1.425 V
Worst Case VCCI = 3.0 V
Advanced I/O Banks

I/O Standard	Drive Strength (mA)	Slew Rate	Capacitive Load (pF)	External Resistor (Ω)	t_{DOUT} (ns)	t_{DP} (ns)	t_{DIN} (ns)	t_{PY} (ns)	t_{EOUT} (ns)	t_{ZL} (ns)	t_{ZH} (ns)	t_{LZ} (ns)	t_{HZ} (ns)	t_{ZLS} (ns)	t_{ZHS} (ns)	Units
3.3 V LVTTL / 3.3 V LVCMOS	12 mA	High	35 pF	–	0.55	3.36	0.04	0.97	0.39	3.42	1.56	3.05	1.94	5.55	2.80	ns
2.5 V LVCMOS	12 mA	High	35 pF	–	0.55	3.39	0.04	1.23	0.39	3.45	3.27	1.83	1.86	5.58	5.39	ns
1.8 V LVCMOS	12 mA	High	35 pF	–	0.55	3.36	0.04	1.16	0.39	1.95	1.68	3.52	3.88	3.16	2.92	ns
1.5 V LVCMOS	12 mA	High	35 pF	–	0.55	3.88	0.04	1.37	0.39	2.25	1.98	3.75	4.00	3.46	3.21	ns
3.3 V PCI	Per PCI spec	High	10 pF	25[2]	0.55	2.19	0.04	0.81	0.39	1.27	0.94	2.65	3.06	2.49	2.18	ns
3.3 V PCI-X	Per PCI-X spec	High	10 pF	25[2]	0.55	2.55	0.04	0.79	0.39	1.27	0.94	2.65	3.06	2.49	2.18	ns
LVDS	24 mA	High	–	–	0.55	1.74	0.04	1.52	–	–	–	–	–	–	–	ns
LVPECL	24 mA	High	–	–	0.55	1.71	0.04	1.34	–	–	–	–	–	–	–	ns

Notes:

1. *For specific junction temperature and voltage supply levels, refer to Table 2-5 on page 2-5 for derating values.*
2. *Resistance is used to measure I/O propagation delays as defined in PCI specifications. See Figure 2-11 on page 2-48 for connectivity. This resistor is not required during normal operation.*

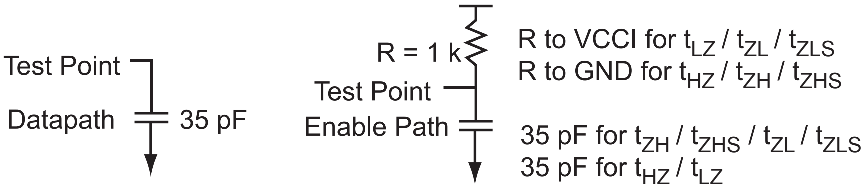


Figure 2-7 • **AC Loading**

Table 2-34 • **AC Waveforms, Measuring Points, and Capacitive Loads**

Input Low (V)	Input High (V)	Measuring Point* (V)	C_{LOAD} (pF)
0	3.3	1.4	35

Note: _*Measuring point = $V_{trip.}$ See Table 2-18 on page 2-17 for a complete table of trip points._

Table 2-37 • **3.3 V LVTTL / 3.3 V LVCMOS High Slew**
Automotive-Case Conditions: T_J = 135°C, Worst-Case VCC = 1.425 V, Worst-Case VCCI = 3.0 V
Applicable to Standard Plus I/O Banks

Drive Strength	Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	t_{ZLS}	t_{ZHS}	Units
4 mA	STD	0.64	8.06	0.05	1.12	0.46	8.20	7.03	1.26	1.27	8.20	7.027	ns
	-1	0.55	6.85	0.04	.095	0.39	6.98	5.98	1.26	1.27	6.98	5.978	ns
6 mA	STD	0.64	5.03	0.05	1.12	0.46	5.13	4.27	1.42	1.56	5.13	4.267	ns
	-1	0.55	4.28	0.04	0.95	0.39	4.36	3.63	1.42	1.56	4.36	3.63	ns
8 mA	STD	0.64	5.03	0.05	1.12	0.46	5.13	4.27	1.42	1.56	5.13	4.267	ns
	-1	0.55	4.28	0.04	0.95	0.39	4.36	3.63	1.42	1.56	4.36	3.63	ns
12 mA	STD	0.64	3.53	0.05	1.12	0.46	1.74	1.43	3.12	3.60	1.74	1.427	ns
	-1	0.55	3.01	0.04	0.95	0.39	1.74	1.43	2.65	3.06	1.74	1.428	ns
16 mA	STD	0.64	3.53	0.05	1.12	0.46	1.74	1.43	3.12	3.60	1.74	1.427	ns
	-1	0.55	3.01	0.04	0.95	0.39	1.74	1.43	2.65	3.06	1.74	1.428	ns

Notes:

1. *Software default selection highlighted in gray.*
2. *For specific junction temperature and voltage supply levels, refer to Table 2-5 on page 2-5 for derating values.*

Table 2-38 • **3.3 V LVTTL / 3.3 V LVCMOS Low Slew**
Automotive-Case Conditions: T_J = 135°C, Worst-Case VCC = 1.425 V, Worst-Case VCCI = 3.0 V
Applicable to Standard Plus I/O Banks

Drive Strength	Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	t_{ZLS}	t_{ZHS}	Units
4 mA	STD	0.64	10.82	0.05	1.12	0.46	11.02	9.42	1.26	1.20	11.02	9.419	ns
	-1	0.55	9.21	0.04	0.95	0.39	9.38	8.01	1.26	1.20	9.38	8.012	ns
6 mA	STD	0.64	7.49	0.05	1.12	0.46	7.63	6.58	1.43	1.48	7.63	6.58	ns
	-1	0.55	6.37	0.04	0.95	0.39	6.49	5.60	1.43	1.49	6.49	5.598	ns
8 mA	STD	0.64	7.49	0.05	1.12	0.46	7.63	6.58	1.43	1.48	7.63	6.58	ns
	-1	0.55	6.37	0.04	0.95	0.39	6.49	5.60	1.43	1.49	6.49	5.598	ns
12 mA	STD	0.64	5.64	0.05	1.12	0.46	5.75	5.04	1.54	1.67	5.75	5.042	ns
	-1	0.55	4.80	0.04	0.95	0.39	4.89	4.29	1.54	1.67	4.89	4.289	ns
16 mA	STD	0.64	5.64	0.05	1.12	0.46	5.75	5.04	1.54	1.67	5.75	5.042	ns
	-1	0.55	4.80	0.04	0.95	0.39	4.89	4.29	1.54	1.67	4.89	4.289	ns

Note: For specific junction temperature and voltage supply levels, refer to Table 2-5 on page 2-5 for derating values.

Timing Characteristics

Table 2-68 • **1.5 V LVCMOS High Slew**
Automotive-Case Conditions: T_J = 135°C, Worst-Case VCC = 1.425 V, Worst-Case VCCI = 2.3 V
Applicable to Advanced I/O Banks

Drive Strength	Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	t_{ZLS}	t_{ZHS}	Units
2 mA	STD	0.64	9.35	0.05	1.61	0.46	7.63	9.35	1.87	1.50	10.13	11.851	ns
	-1	0.55	7.95	0.04	1.37	0.39	6.49	7.95	1.87	1.50	8.62	10.081	ns
4 mA	STD	0.64	5.94	0.05	1.61	0.46	5.42	5.94	2.07	1.84	7.92	8.442	ns
	-1	0.55	5.05	0.04	1.37	0.39	4.61	5.05	2.07	1.85	6.74	7.181	ns
6 mA	STD	0.64	5.22	0.05	1.61	0.46	5.09	5.22	2.11	1.93	7.59	7.718	ns
	-1	0.55	4.44	0.04	1.37	0.39	4.33	4.44	2.11	1.93	6.45	6.566	ns
8 mA	STD	0.64	4.56	0.05	1.61	0.46	2.25	1.98	4.41	4.70	3.46	3.211	ns
	-1	0.55	3.88	0.04	1.37	0.39	2.25	1.98	3.75	4.00	3.46	3.213	ns
12 mA	STD	0.64	4.56	0.05	1.61	0.46	2.25	1.98	4.41	4.70	3.46	3.211	ns
	-1	0.55	3.88	0.04	1.37	0.39	2.25	1.98	3.75	4.00	3.46	3.213	ns

Notes:

1. *Software default selection highlighted in gray.*
2. *For specific junction temperature and voltage supply levels, refer to Table 2-5 on page 2-5 for derating values.*

Table 2-69 • **1.5 V LVCMOS Low Slew**
Automotive-Case Conditions: T_J = 135°C, Worst-Case VCC = 1.425 V, Worst-Case VCCI = 2.3 V
Applicable to Advanced I/O Banks

Drive Strength	Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	t_{ZLS}	t_{ZHS}	Units
2 mA	STD	0.64	14.29	0.05	1.45	0.46	14.32	14.29	1.88	1.43	16.82	16.794	ns
	-1	0.55	12.16	0.04	1.23	0.39	12.18	12.16	1.88	1.43	14.31	14.286	ns
4 mA	STD	0.64	11.19	0.05	1.45	0.46	11.40	10.67	2.07	1.77	13.90	13.175	ns
	-1	0.55	9.52	0.04	1.23	0.39	9.70	9.08	2.07	1.77	11.82	11.207	ns
6 mA	STD	0.64	10.44	0.05	1.45	0.46	10.63	9.94	2.12	1.86	13.13	12.442	ns
	-1	0.55	8.88	0.04	1.23	0.39	9.04	8.46	2.12	1.86	11.17	10.584	ns
8 mA	STD	0.64	9.96	0.05	1.45	0.46	10.15	9.94	2.18	2.19	12.65	12.445	ns
	-1	0.55	8.47	0.04	1.23	0.39	8.63	8.46	2.19	2.20	10.76	10.586	ns
12 mA	STD	0.64	9.96	0.05	1.45	0.46	10.15	9.94	2.18	2.19	12.65	12.445	ns
	-1	0.55	8.47	0.04	1.23	0.39	8.63	8.46	2.19	2.20	10.76	10.586	ns

Note: For specific junction temperature and voltage supply levels, refer to Table 2-5 on page 2-5 for derating values.

Table 2-90 • **Parameter Definition and Measuring Nodes**

Parameter Name	Parameter Definition	Measuring Nodes (from, to)*
t_{OCLKQ}	Clock-to-Q of the Output Data Register	H, DOUT
t_{OSUD}	Data Setup Time for the Output Data Register	F, H
t_{OHD}	Data Hold Time for the Output Data Register	F, H
t_{OSUE}	Enable Setup Time for the Output Data Register	G, H
t_{OHE}	Enable Hold Time for the Output Data Register	G, H
t_{OPRE2Q}	Asynchronous Preset-to-Q of the Output Data Register	L, DOUT
$t_{OREMPRE}$	Asynchronous Preset Removal Time for the Output Data Register	L, H
$t_{ORECPRE}$	Asynchronous Preset Recovery Time for the Output Data Register	L, H
t_{OECLKQ}	Clock-to-Q of the Output Enable Register	H, EOUT
t_{OESUD}	Data Setup Time for the Output Enable Register	J, H
t_{OEHD}	Data Hold Time for the Output Enable Register	J, H
t_{OESUE}	Enable Setup Time for the Output Enable Register	K, H
t_{OEHE}	Enable Hold Time for the Output Enable Register	K, H
$t_{OEPRE2Q}$	Asynchronous Preset-to-Q of the Output Enable Register	I, EOUT
$t_{OEREMPRE}$	Asynchronous Preset Removal Time for the Output Enable Register	I, H
$t_{OERECPRE}$	Asynchronous Preset Recovery Time for the Output Enable Register	I, H
t_{ICLKQ}	Clock-to-Q of the Input Data Register	A, E
t_{ISUD}	Data Setup Time for the Input Data Register	C, A
t_{IHD}	Data Hold Time for the Input Data Register	C, A
t_{ISUE}	Enable Setup Time for the Input Data Register	B, A
t_{IHE}	Enable Hold Time for the Input Data Register	B, A
t_{IPRE2Q}	Asynchronous Preset-to-Q of the Input Data Register	D, E
$t_{IREMPRE}$	Asynchronous Preset Removal Time for the Input Data Register	D, A
$t_{IRECPRE}$	Asynchronous Preset Recovery Time for the Input Data Register	D, A

*Note: *See Figure 2-15 on page 2-53 for more information.*

Table 2-91 • **Parameter Definitions and Measuring Nodes**

Parameter Name	Parameter Definition	Measuring Nodes (from, to)*
t_{OCLKQ}	Clock-to-Q of the Output Data Register	HH, DOUT
t_{OSUD}	Data Setup Time for the Output Data Register	FF, HH
t_{OHD}	Data Hold Time for the Output Data Register	FF, HH
t_{OSUE}	Enable Setup Time for the Output Data Register	GG, HH
t_{OHE}	Enable Hold Time for the Output Data Register	GG, HH
t_{OCLR2Q}	Asynchronous Clear-to-Q of the Output Data Register	LL, DOUT
$t_{OREMCLR}$	Asynchronous Clear Removal Time for the Output Data Register	LL, HH
$t_{ORECCLR}$	Asynchronous Clear Recovery Time for the Output Data Register	LL, HH
t_{OECLKQ}	Clock-to-Q of the Output Enable Register	HH, EOUT
t_{OESUD}	Data Setup Time for the Output Enable Register	JJ, HH
t_{OEHD}	Data Hold Time for the Output Enable Register	JJ, HH
t_{OESUE}	Enable Setup Time for the Output Enable Register	KK, HH
t_{OEHE}	Enable Hold Time for the Output Enable Register	KK, HH
$t_{OECLR2Q}$	Asynchronous Clear-to-Q of the Output Enable Register	II, EOUT
$t_{OEREMCLR}$	Asynchronous Clear Removal Time for the Output Enable Register	II, HH
$t_{OERECCLR}$	Asynchronous Clear Recovery Time for the Output Enable Register	II, HH
t_{ICLKQ}	Clock-to-Q of the Input Data Register	AA, EE
t_{ISUD}	Data Setup Time for the Input Data Register	CC, AA
t_{IHD}	Data Hold Time for the Input Data Register	CC, AA
t_{ISUE}	Enable Setup Time for the Input Data Register	BB, AA
t_{IHE}	Enable Hold Time for the Input Data Register	BB, AA
t_{ICLR2Q}	Asynchronous Clear-to-Q of the Input Data Register	DD, EE
$t_{IREMCLR}$	Asynchronous Clear Removal Time for the Input Data Register	DD, AA
$t_{IRECCLR}$	Asynchronous Clear Recovery Time for the Input Data Register	DD, AA

*Note: *See Figure 2-16 on page 2-55 for more information.*

VersaTile Characteristics

VersaTile Specifications as a Combinatorial Module

The ProASIC3 library offers all combinations of LUT-3 combinatorial functions. In this section, timing characteristics are presented for a sample of the library. For more details, refer to the *Fusion, IGLOO/e, and ProASIC3/E Macro Library Guide*.

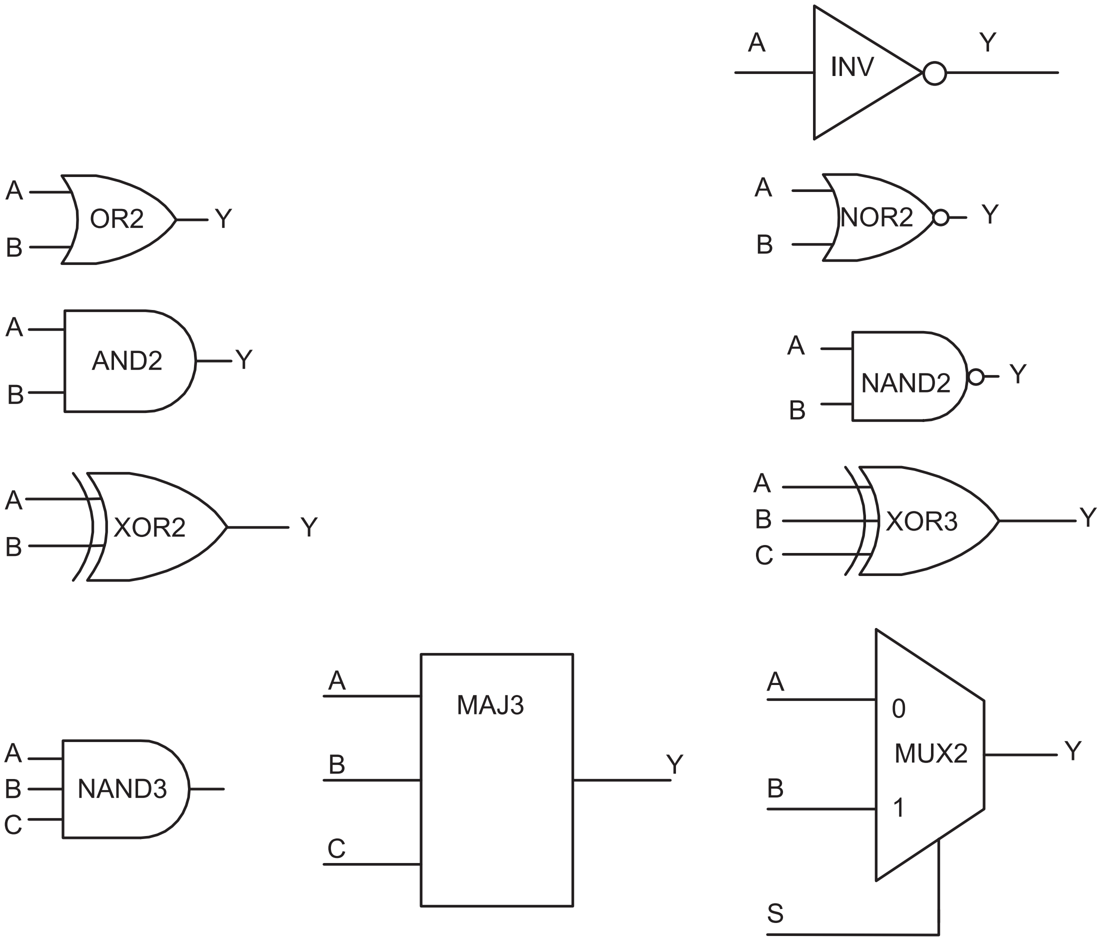


Figure 2-24 • **Sample of Combinatorial Cells**

Global Resource Characteristics

A3P250 Clock Tree Topology

Clock delays are device-specific. Figure 2-28 is an example of a global tree used for clock routing. The global tree presented in Figure 2-28 is driven by a CCC located on the west side of the A3P250 device. It is used to drive all D-flip-flops in the device.

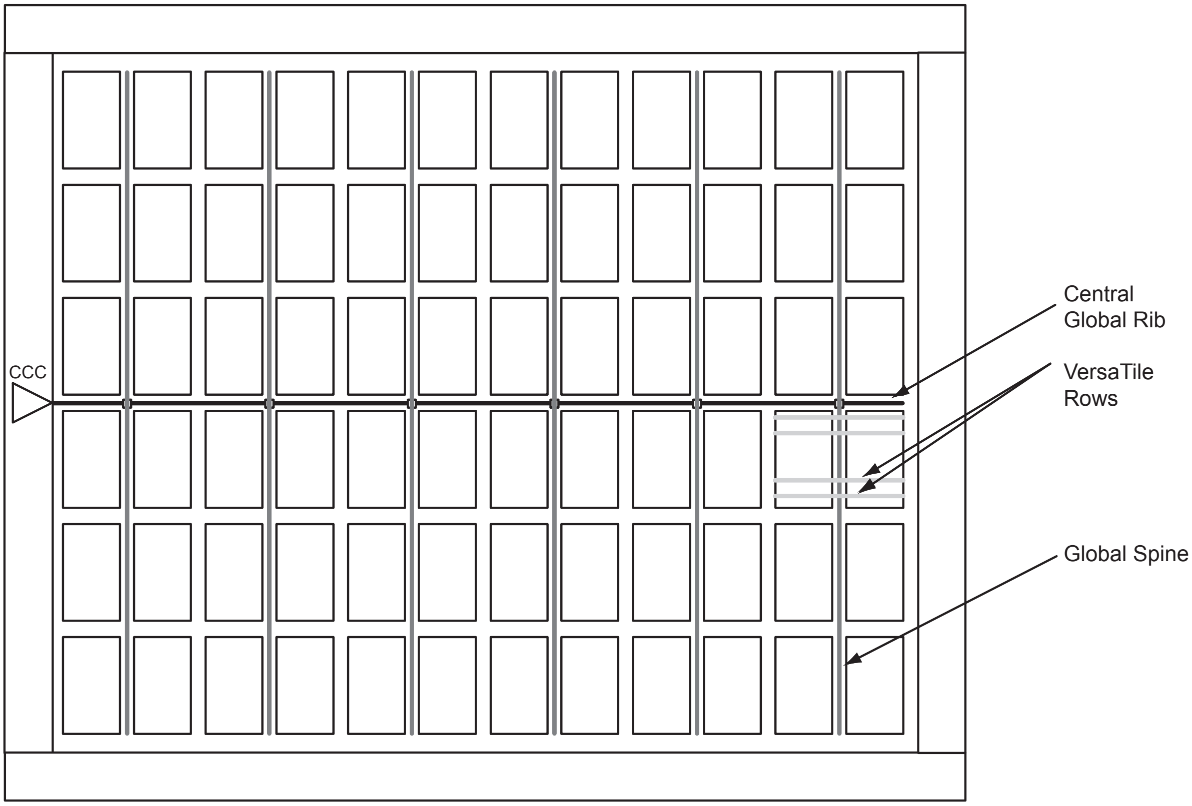


Figure 2-28 • **Example of Global Tree Use in an A3P250 Device for Clock Routing**

Timing Waveforms

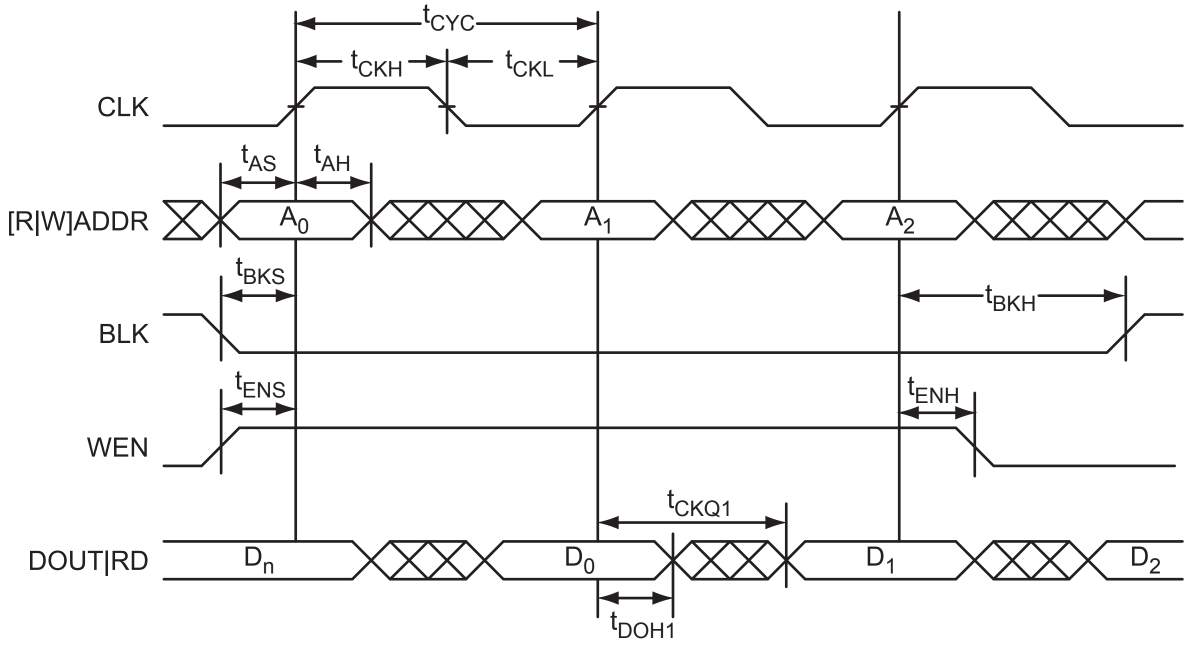


***Figure 2-31* • RAM Read for Pass-Through Output. Applicable to Both RAM4K9 and RAM512x18.**

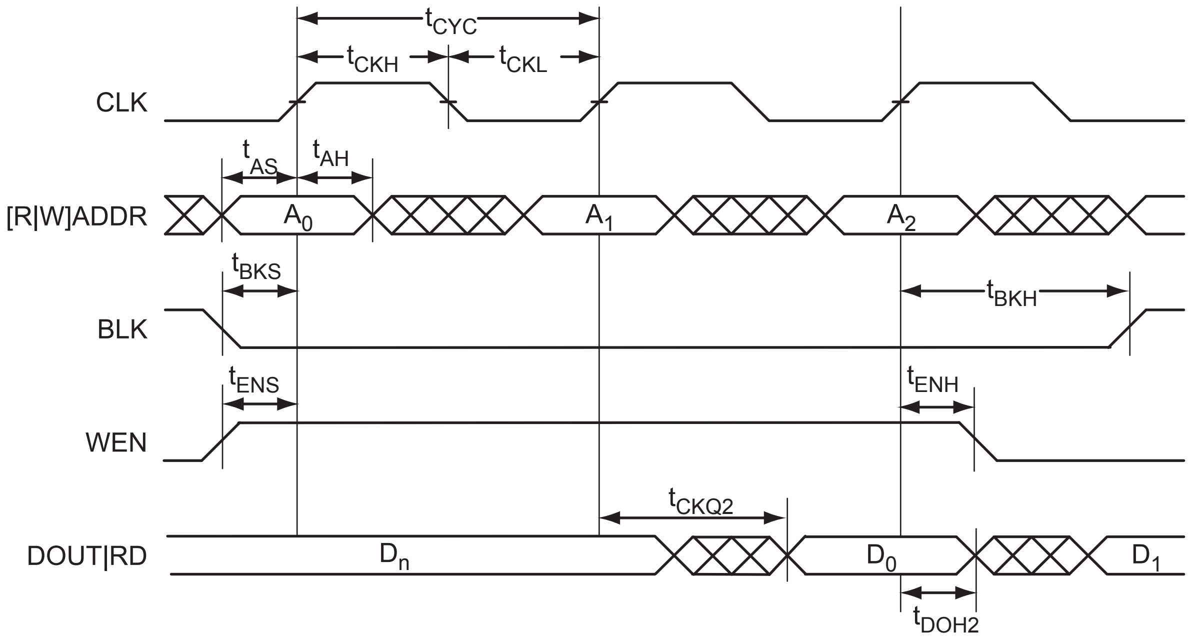


***Figure 2-32* • RAM Read for Pipelined Output. Applicable to Both RAM4K9 and RAM512x18.**

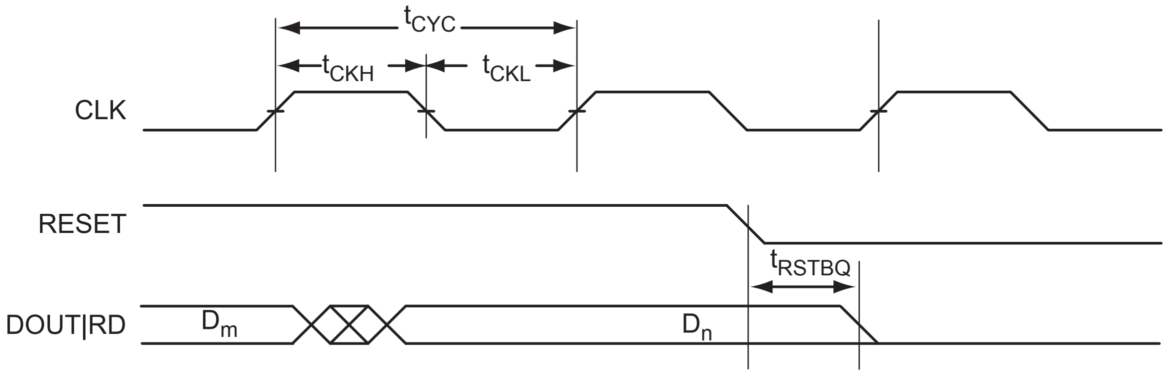


Figure 2-35 • **RAM Reset. Applicable to Both RAM4K9 and RAM512x18**

VQ100	
Pin Number	A3P250 Function
1	GND
2	GAA2/IO118UDB3
3	IO118VDB3
4	GAB2/IO117UDB3
5	IO117VDB3
6	GAC2/IO116UDB3
7	IO116VDB3
8	IO112PSB3
9	GND
10	GFB1/IO109PDB3
11	GFB0/IO109NDB3
12	VCOMPLF
13	GFA0/IO108NPB3
14	VCCPLF
15	GFA1/IO108PPB3
16	GFA2/IO107PSB3
17	VCC
18	VCCIB3
19	GFC2/IO105PSB3
20	GEC1/IO100PDB3
21	GEC0/IO100NDB3
22	GEA1/IO98PDB3
23	GEA0/IO98NDB3
24	VMV3
25	GNDQ
26	GEA2/IO97RSB2
27	GEB2/IO96RSB2
28	GEC2/IO95RSB2
29	IO93RSB2
30	IO92RSB2
31	IO91RSB2
32	IO90RSB2
33	IO88RSB2
34	IO86RSB2
35	IO85RSB2
36	IO84RSB2
37	VCC
38	GND
39	VCCIB2
40	IO77RSB2
41	IO74RSB2
42	IO71RSB2
43	GDC2/IO63RSB2
44	GDB2/IO62RSB2
45	GDA2/IO61RSB2
46	GNDQ
47	TCK
48	TDI
49	TMS
50	VMV2
51	GND
52	VPUMP
53	NC
54	TDO
55	TRST
56	VJTAG
57	GDA1/IO60USB1
58	GDC0/IO58VDB1
59	GDC1/IO58UDB1
60	IO52NDB1
61	GCB2/IO52PDB1
62	GCA1/IO50PDB1
63	GCA0/IO50NDB1
64	GCC0/IO48NDB1
65	GCC1/IO48PDB1
66	VCCIB1
67	GND
68	VCC
69	IO43NDB1
70	GBC2/IO43PDB1
71	GBB2/IO42PSB1
72	IO41NDB1
73	GBA2/IO41PDB1
74	VMV1
75	GNDQ
76	GBA1/IO40RSB0
77	GBA0/IO39RSB0
78	GBB1/IO38RSB0
79	GBB0/IO37RSB0
80	GBC1/IO36RSB0
81	GBC0/IO35RSB0
82	IO29RSB0
83	IO27RSB0
84	IO25RSB0
85	IO23RSB0
86	IO21RSB0
87	VCCIB0
88	GND
89	VCC
90	IO15RSB0
91	IO13RSB0
92	IO11RSB0
93	GAC1/IO05RSB0
94	GAC0/IO04RSB0
95	GAB1/IO03RSB0
96	GAB0/IO02RSB0
97	GAA1/IO01RSB0
98	GAA0/IO00RSB0
99	GNDQ
100	VMV0

FG144	
Pin Number	A3P060 Function
K1	GEB0/IO74RSB1
K2	GEA1/IO73RSB1
K3	GEA0/IO72RSB1
K4	GEA2/IO71RSB1
K5	IO65RSB1
K6	IO64RSB1
K7	GND
K8	IO57RSB1
K9	GDC2/IO56RSB1
K10	GND
K11	GDA0/IO50RSB0
K12	GDB0/IO48RSB0
L1	GND
L2	VMV1
L3	GEB2/IO70RSB1
L4	IO67RSB1
L5	VCCIB1
L6	IO62RSB1
L7	IO59RSB1
L8	IO58RSB1
L9	TMS
L10	VJTAG
L11	VMV1
L12	TRST
M1	GNDQ
M2	GEC2/IO69RSB1
M3	IO68RSB1
M4	IO66RSB1
M5	IO63RSB1
M6	IO61RSB1
M7	IO60RSB1
M8	NC
M9	TDI
M10	VCCIB1
M11	VPUMP
M12	GNDQ

FG144	
Pin Number	A3P1000 Function
A1	GNDQ
A2	VMV0
A3	GAB0/IO02RSB0
A4	GAB1/IO03RSB0
A5	IO10RSB0
A6	GND
A7	IO44RSB0
A8	VCC
A9	IO69RSB0
A10	GBA0/IO76RSB0
A11	GBA1/IO77RSB0
A12	GNDQ
B1	GAB2/IO224PDB3
B2	GND
B3	GAA0/IO00RSB0
B4	GAA1/IO01RSB0
B5	IO13RSB0
B6	IO26RSB0
B7	IO35RSB0
B8	IO60RSB0
B9	GBB0/IO74RSB0
B10	GBB1/IO75RSB0
B11	GND
B12	VMV1
C1	IO224NDB3
C2	GFA2/IO206PPB3
C3	GAC2/IO223PDB3
C4	VCC
C5	IO16RSB0
C6	IO29RSB0
C7	IO32RSB0
C8	IO63RSB0
C9	IO66RSB0
C10	GBA2/IO78PDB1
C11	IO78NDB1
C12	GBC2/IO80PPB1
D1	IO213PDB3
D2	IO213NDB3
D3	IO223NDB3
D4	GAA2/IO225PPB3
D5	GAC0/IO04RSB0
D6	GAC1/IO05RSB0
D7	GBC0/IO72RSB0
D8	GBC1/IO73RSB0
D9	GBB2/IO79PDB1
D10	IO79NDB1
D11	IO80NPB1
D12	GCB1/IO92PPB1
E1	VCC
E2	GFC0/IO209NDB3
E3	GFC1/IO209PDB3
E4	VCCIB3
E5	IO225NPB3
E6	VCCIB0
E7	VCCIB0
E8	GCC1/IO91PDB1
E9	VCCIB1
E10	VCC
E11	GCA0/IO93NDB1
E12	IO94NDB1
F1	GFB0/IO208NPB3
F2	VCOMPLF
F3	GFB1/IO208PPB3
F4	IO206NPB3
F5	GND
F6	GND
F7	GND
F8	GCC0/IO91NDB1
F9	GCB0/IO92NPB1
F10	GND
F11	GCA1/IO93PDB1
F12	GCA2/IO94PDB1
G1	GFA1/IO207PPB3
G2	GND
G3	VCCPLF
G4	GFA0/IO207NPB3
G5	GND
G6	GND
G7	GND
G8	GDC1/IO111PPB1
G9	IO96NDB1
G10	GCC2/IO96PDB1
G11	IO95NDB1
G12	GCB2/IO95PDB1
H1	VCC
H2	GFB2/IO205PDB3
H3	GFC2/IO204PSB3
H4	GEC1/IO190PDB3
H5	VCC
H6	IO105PDB1
H7	IO105NDB1
H8	GDB2/IO115RSB2
H9	GDC0/IO111NPB1
H10	VCCIB1
H11	IO101PSB1
H12	VCC
J1	GEB1/IO189PDB3
J2	IO205NDB3
J3	VCCIB3
J4	GEC0/IO190NDB3
J5	IO160RSB2
J6	IO157RSB2
J7	VCC
J8	TCK
J9	GDA2/IO114RSB2
J10	TDO
J11	GDA1/IO113PDB1
J12	GDB1/IO112PDB1

FG256	
Pin Number	**A3P250 Function**
P9	IO76RSB2
P10	IO71RSB2
P11	IO66RSB2
P12	NC
P13	TCK
P14	VPUMP
P15	TRST
P16	GDA0/IO60VDB1
R1	GEA1/IO98PDB3
R2	GEA0/IO98NDB3
R3	NC
R4	GEC2/IO95RSB2
R5	IO91RSB2
R6	IO88RSB2
R7	IO84RSB2
R8	IO80RSB2
R9	IO77RSB2
R10	IO72RSB2
R11	IO68RSB2
R12	IO65RSB2
R13	GDB2/IO62RSB2
R14	TDI
R15	NC
R16	TDO
T1	GND
T2	IO94RSB2
T3	GEB2/IO96RSB2
T4	IO93RSB2
T5	IO90RSB2
T6	IO87RSB2
T7	IO83RSB2
T8	IO79RSB2
T9	IO78RSB2
T10	IO73RSB2
T11	IO70RSB2
T12	GDC2/IO63RSB2
T13	IO67RSB2
T14	GDA2/IO61RSB2
T15	TMS
T16	GND

Revision	Changes	Page
Revision 2 (continued)	The "Pin Descriptions and Packaging" chapter has been added (SAR 34767),	3-1
	The "VQ100" pin table for A3P125 has been added (SAR 37944).	4-3
	Package names used in the "Package Pin Assignments" section were revised to match standards given in *Package Mechanical Drawings* (SAR 34767).	4-1
July 2010	The versioning system for datasheets has been changed. Datasheets are assigned a revision number that increments each time the datasheet is revised. The "Automotive ProASIC3 Device Status" table on page II indicates the status for each device in the device family.	N/A

Revision	Changes	Page
Revision 1 (Dec 2009) Product Brief v1.1	The QNG132 package was added to the "Automotive ProASIC3 Product Family" table, "I/Os Per Package" table, "Automotive ProASIC3 Ordering Information", and "Temperature Grade Offerings".	I – IV
Packaging v1.1	Pin tables for A3P125 and A3P250 were added for the "QN132" package.	4-6